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frequency of the cavity due to the sample, and the imaginary component is calculated
from a change in cavity Q. The accuracy of these measurements depends upon two
general sources of error: 1) the accuracy of the cavity characterization; and 2) the
material properties such as density and uniformity of shape. The error due to the cavity
characterization results in an accuracy of approximately $\pm 2\%$ for the real part of the
dielectric constant, and limits the resolution of the loss tangent (the imaginary component
divided by the real component of the dielectric constant) to approximately 0.001. The
error due to material properties and sample shape can be considerably greater than the
cavity characterization error, particularly the error due to low material density; hence the
densities of bulk materials are reported in the Density GM/CC column of TABLE I.

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Delete the paragraph at page 14, lines 8-9 and replace the deleted paragraph with the following
replacement paragraph:

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In addition to numerous devices already disclosed throughout this specification,
the following examples illustrate two specific devices composed of $\text{Sr}_2\text{RESbO}_6$
compounds in accordance with this invention.

IN THE CLAIMS:

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4. (Amended) The dielectric substrate, according to claim 3, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 15.1; and
said dielectric substrate having a low dielectric loss of less than 1×10^{-3} .

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SUB B3
7. (Amended) The dielectric substrate, according to claim 6, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 5.1; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

10. (Amended) The dielectric substrate, according to claim 9, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 10.0; and
said dielectric substrate having a low dielectric loss of 2.0×10^{-3} .

13. (Amended) The dielectric substrate, according to claim 12, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 5.3; and
said dielectric substrate having a low dielectric loss of 1.6×10^{-3} .

16. The (Amended) dielectric substrate, according to claim 15, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 11.6; and
said dielectric substrate having a low dielectric loss of about 3.1×10^{-3} .

19. (Amended) The dielectric substrate, according to claim 18, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 11.2; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

22. (Amended) The dielectric substrate, according to claim 21, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 12.9; and
said dielectric substrate having a low dielectric loss of 1.4×10^{-3} .

25. (Amended) The dielectric substrate, according to claim 24, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 7.1; and
said dielectric substrate having a low dielectric loss of 1.4×10^{-3} .

28. (Amended) The dielectric substrate, according to claim 27, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 16.3; and
said dielectric substrate having a low dielectric loss of 3.8×10^{-3} .

31. (Amended) The dielectric substrate, according to claim 30, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 12.1; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

34. (Amended) The dielectric substrate, according to claim 33, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 13.6; and
said dielectric substrate having a low dielectric loss of less than 1.0×10^{-3} .

37. (Amended) The dielectric substrate, according to claim 36, further comprising:
said dielectric substrate is constructed in a bulk form;
said dielectric substrate having a low dielectric constant of 10.9; and
said dielectric substrate having a low dielectric loss of 2.2×10^{-3} .